



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/585,744	07/12/2006	Akira Bandoh	Q81505	1506
23373	7590	03/25/2010	EXAMINER	
SUGHRUE MION, PLLC			AHMED, SELIM U	
2100 PENNSYLVANIA AVENUE, N.W.				
SUITE 800			ART UNIT	PAPER NUMBER
WASHINGTON, DC 20037			2826	
			NOTIFICATION DATE	DELIVERY MODE
			03/25/2010	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

sughrue@sughrue.com
PPROCESSING@SUGHRUE.COM
USPTO@SUGHRUE.COM

Advisory Action Before the Filing of an Appeal Brief	Application No.	Applicant(s)
	10/585,744	BANDOH ET AL.
	Examiner	Art Unit
	SELIM AHMED	2826

--The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

THE REPLY FILED 01 March 2010 FAILS TO PLACE THIS APPLICATION IN CONDITION FOR ALLOWANCE.

1. The reply was filed after a final rejection, but prior to or on the same day as filing a Notice of Appeal. To avoid abandonment of this application, applicant must timely file one of the following replies: (1) an amendment, affidavit, or other evidence, which places the application in condition for allowance; (2) a Notice of Appeal (with appeal fee) in compliance with 37 CFR 41.31; or (3) a Request for Continued Examination (RCE) in compliance with 37 CFR 1.114. The reply must be filed within one of the following time periods:

- a) The period for reply expires _____ months from the mailing date of the final rejection.
 - b) The period for reply expires on: (1) the mailing date of this Advisory Action, or (2) the date set forth in the final rejection, whichever is later. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of the final rejection.
- Examiner Note: If box 1 is checked, check either box (a) or (b). ONLY CHECK BOX (b) WHEN THE FIRST REPLY WAS FILED WITHIN TWO MONTHS OF THE FINAL REJECTION. See MPEP 706.07(f).

Extensions of time may be obtained under 37 CFR 1.136(a). The date on which the petition under 37 CFR 1.136(a) and the appropriate extension fee have been filed is the date for purposes of determining the period of extension and the corresponding amount of the fee. The appropriate extension fee under 37 CFR 1.17(a) is calculated from: (1) the expiration date of the shortened statutory period for reply originally set in the final Office action; or (2) as set forth in (b) above, if checked. Any reply received by the Office later than three months after the mailing date of the final rejection, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

NOTICE OF APPEAL

2. The Notice of Appeal was filed on _____. A brief in compliance with 37 CFR 41.37 must be filed within two months of the date of filing the Notice of Appeal (37 CFR 41.37(a)), or any extension thereof (37 CFR 41.37(e)), to avoid dismissal of the appeal. Since a Notice of Appeal has been filed, any reply must be filed within the time period set forth in 37 CFR 41.37(a).

AMENDMENTS

3. The proposed amendment(s) filed after a final rejection, but prior to the date of filing a brief, will not be entered because
- (a) They raise new issues that would require further consideration and/or search (see NOTE below);
 - (b) They raise the issue of new matter (see NOTE below);
 - (c) They are not deemed to place the application in better form for appeal by materially reducing or simplifying the issues for appeal; and/or
 - (d) They present additional claims without canceling a corresponding number of finally rejected claims.

NOTE: _____. (See 37 CFR 1.116 and 41.33(a)).

4. The amendments are not in compliance with 37 CFR 1.121. See attached Notice of Non-Compliant Amendment (PTOL-324).
5. Applicant's reply has overcome the following rejection(s): _____.
6. Newly proposed or amended claim(s) _____ would be allowable if submitted in a separate, timely filed amendment canceling the non-allowable claim(s).

7. For purposes of appeal, the proposed amendment(s): a) will not be entered, or b) will be entered and an explanation of how the new or amended claims would be rejected is provided below or appended.

The status of the claim(s) is (or will be) as follows:

Claim(s) allowed: _____.

Claim(s) objected to: _____.

Claim(s) rejected: 37 and 55-66.

Claim(s) withdrawn from consideration: _____.

AFFIDAVIT OR OTHER EVIDENCE

8. The affidavit or other evidence filed after a final action, but before or on the date of filing a Notice of Appeal will not be entered because applicant failed to provide a showing of good and sufficient reasons why the affidavit or other evidence is necessary and was not earlier presented. See 37 CFR 1.116(e).
9. The affidavit or other evidence filed after the date of filing a Notice of Appeal, but prior to the date of filing a brief, will not be entered because the affidavit or other evidence failed to overcome all rejections under appeal and/or appellant fails to provide a showing of good and sufficient reasons why it is necessary and was not earlier presented. See 37 CFR 41.33(d)(1).

10. The affidavit or other evidence is entered. An explanation of the status of the claims after entry is below or attached.

REQUEST FOR RECONSIDERATION/OTHER

11. The request for reconsideration has been considered but does NOT place the application in condition for allowance because:
See note below.
12. Note the attached Information Disclosure Statement(s). (PTO/SB/08) Paper No(s). _____
13. Other: _____.

/Sue A. Purvis/
Supervisory Patent Examiner, Art Unit 2826

Applicant's remark filed on 03/01/2010 has been fully considered but found not persuasive. On page of the remark applicant argued, "Although Guo teaches a superlattice with 5-15 repetitions of layers 20 and 22 having a thickness on the order of 10 nm or less, the Examiner has not identified a reason that would have prompted a person of ordinary skill in the relevant field to combine (or modify) the elements in the way that the claimed new invention does. KSR International Co. The Examiner's reasoning, such as that one would optimize the repetition number and thickness of the superlattice layer, i.e., Applicant's high and low concentration GaN layers for desirable output, is based on improper hindsight."

As indicated in the final rejection sent on 11/30/2009, Kawano lacks the repetition number of said higher concentration layer and said lower concentration layer is 10 to 1000 and a thickness of a repetition cycle being 1 nm to 1000 nm. In para[0012, 0039-0042] and claims 5-8 of Kawano discloses one or more repetition of said higher concentration layer and said lower concentration layer rather. In para[0027] of Kawano discloses a thickness of a repetition cycle is as low as 10 um. So, applicant's claimed device having specific 10 to 1000 repetitions of higher concentration and lower concentration layers with a thickness of 1 nm to 1000 nm while Kawano discloses a device with one or more higher concentration and lower concentration layer with a thickness of as low as 10 um. However, it is well known in the semiconductor fabrication process to optimize certain parameters within a technology using design of experiment (DOE) technique to meet certain product specific performance and reliability. So, it would have been obvious to one of ordinary skill in the art to form the repetition number of 10 to 1000 of said higher concentration layer and said lower concentration layer and a thickness of a repetition cycle within 1 nm to 1000 nm through routine experimentation of the film deposition chemistry and parameters. In another words, it is reasonable to say that it is within the scope of one ordinary skill in the art to form 10 to 1000 repetitions of high and low concentration layers with a thickness of the repetition cycle within 1 nm to 1000 nm since Kawano discloses one or more higher concentration and lower concentration layer with a thickness of a repetition cycle being as low as 10 um. Furthermore, in para[0013] of Guo discloses, "...superlattices introduce compressive strain into the gallium nitride-based semiconductor materials in the structure and, hence, prevent cracking of the gallium nitride based semiconductor layers. Further, it is also believed that the superlattices serve as "filters" which limit propagation of crystalline defects such as those referred to as threading dislocation from the lower layers of the structure upwardly into the operative structure at the top. These factors are believed to contribute to the high crystal quality of the gallium nitride-based semiconductors in the operative structure. Further, it is believed that the superlattices tend to limit diffusion of silicon into the gallium nitride-based semiconductors." So, as Guo pointed out, superlattice serve as a "filter" which limits propagation of crystalline defects contributing high crystal quality. The Examiner referred desirable output as high crystal quality. While Kawano's structure lacks specific thickness and repetitions, Guo discloses Aluminum nitride and Gallium nitride superlattice repetition layers 20, 22 with 5-15 repetitions with a thickness on the order of 10 nm or less. So, it reasonable to assume that one would optimize the repetition number and thickness of the superlattice layer i.e. applicant's high and low concentration GaN layers as shown by Guo for high crystal quality. Thus the Examiner still believes the final rejection sent on 11/30/2009 is proper.

/Sue A. Purvis/
Supervisory Patent Examiner, Art Unit 2826